12V P-Channel Enhancement Mode MOSFET

Description

The CP1216DR-N uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. This device is suitable for use as a load switch or in PWM applications.

General Features

- V_{DS} =-16V，I_D =-16A
  $R_{DS(ON)}$(Typ.)= 15.1mΩ @V_{GS}=-4.5V
  $R_{DS(ON)}$(Typ.)=24.2mΩ @V_{GS}=-2.5V
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

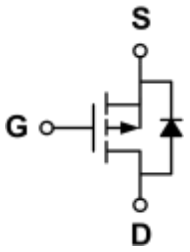
Application

- PWM applications
- Load switch

Package

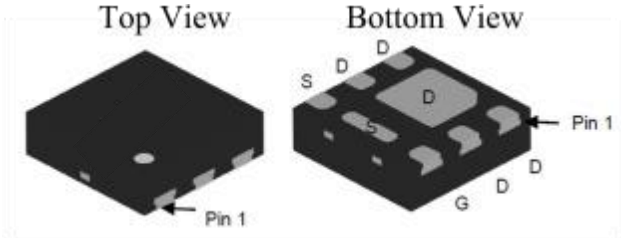
- DFN2*2-6L-B

Schematic diagram



Marking and pin assignment

DFN2*2-6L-B



NP----Natlinear Power

Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
CP1216DR-N-G	-55°C to +150°C	DFN2*2-6L-B	4000

Absolute Maximum Ratings (TA=25℃ unless otherwise noted)

parameter		symbol	limit	unit
Drain-source voltage		V_{DS}	-16	V
Gate-source voltage		V_{GS}	±10	V
Drain current-continuous	T_C=25℃	I_D	-16[a]	A
	T_C=70℃		-16[a]	
	T_A=25℃		-16[a,b,c]	
	T_A=70℃		-12[b,c]	
Drain-source Diode forward current	T_C=25℃	Is	-16[a]	A
	T_A=25℃		-2.9[b,c]	
Maximum power dissipation	T_C=25℃	P_D	2.3	W
	T_C=70℃		1.1	
	T_A=25℃		3.5[b,c]	

	T_A=70℃		2.2[b,c]	
Operating junction Temperature range		Tj	-55—150	℃

Thermal Resistance Ratings

Parameter		Symbol	Typ.	Max.	Unit
Maximum junction-to-ambient[b,d]	t < 5 s	R_{thJA}	20	25	℃/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	45	55	

Notes:

a. Package limited； b. Surface mounted on 1" x 1" FR4 board

c. t = 5 s； d. Maximum under steady state conditions is 80 °C/W

Electrical Characteristics (TA=25℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF Characteristics						
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0V, I_D=-250μA	-16	-	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS}=-12V, V_{GS}=0V	-	-	-1	μA
Gate-body leakage	I_{GSS}	V_{DS}=0V, V_{GS}=±10V	-	-	±100	nA
ON Characteristics						
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-0.5	-0.9	-1.2	V
Drain-source on-state resistance	$R_{DS(ON)}$	V_{GS}=-4.5V, I_D=-10A	-	15.1	20	mΩ
		V_{GS}=-2.5V, I_D=-10A	-	24.2	30	
Forward transconductance	gfs	V_{DS}=-6V, I_D=-8A	-	60	-	S
Dynamic Characteristics						
Input capacitance	C_{ISS}	V_{DS}=-6V ,V_{GS}=0V f=1.0MHz	-	1486	-	pF
Output capacitance	C_{OSS}		-	265	-	
Reverse transfer capacitance	C_{RSS}		-	224	-	
Switching Characteristics						
Turn-on delay time	$t_{D(ON)}$	V_{DD}=-10V I_D=-8A V_{GEN}=-5V R_L=1.2ohm R_{GEN}=1ohm	-	12	-	ns
Rise time	tr		-	34	-	
Turn-off delay time	$t_{D(OFF)}$		-	31	-	
Fall time	tf		-	10	-	
Total gate charge	Qg	V_{DS}=-10V,I_D=-10A V_{GS}=-5V	-	15.1	-	nC
Gate-source charge	Qgs		-	3.7	-	
Gate-drain charge	Qgd		-	3.1	-	
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode forward voltage	V_{SD}	V_{GS}=0V,Is=-10A	-	-0.84	-1.2	V

Typical Performance Characteristics

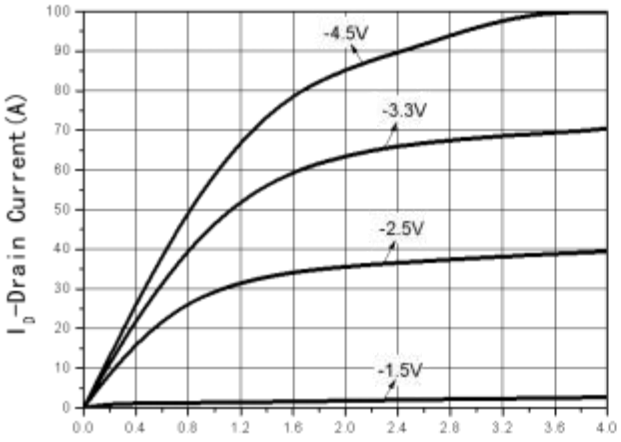


Fig1 Output Characteristics

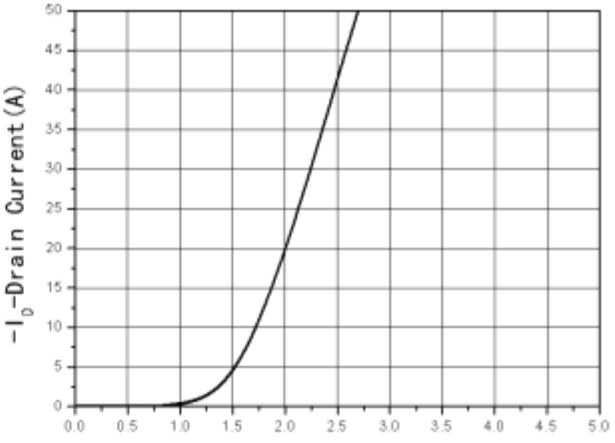


Fig2 Transfer Characteristics

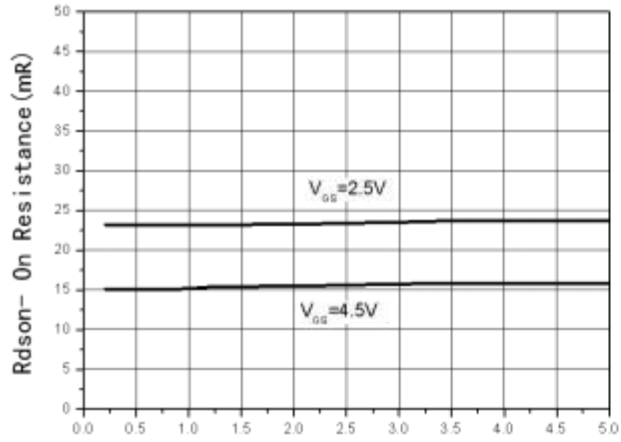


Fig3 Rdson-Drain current

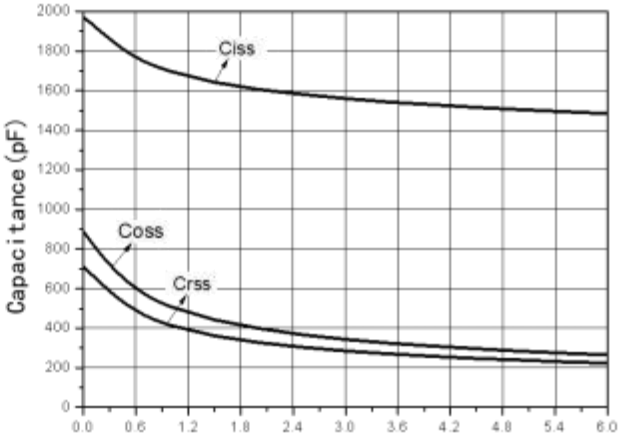


Fig4 Capacitance vs Vds

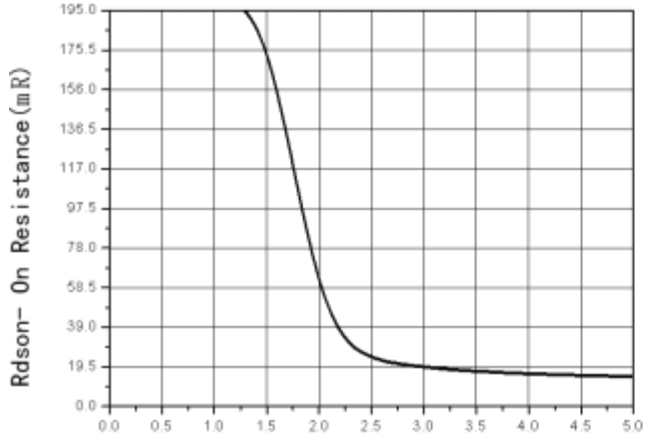


Fig5 Rdson-Gate Drain voltage

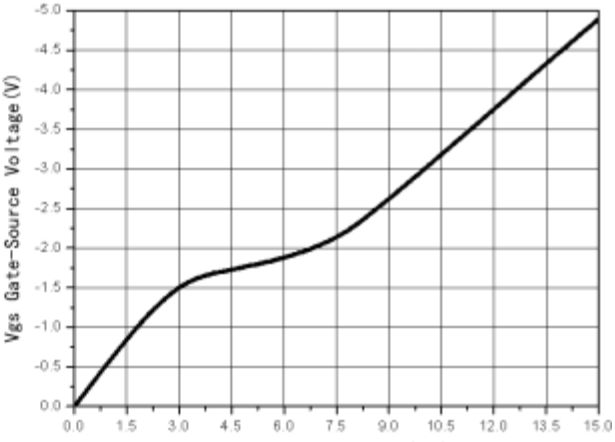
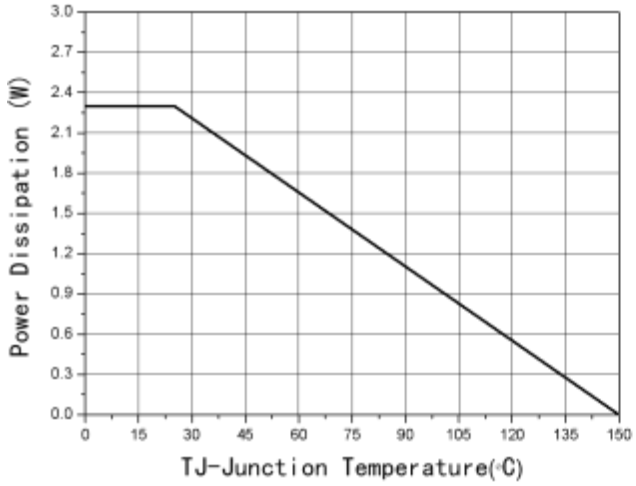
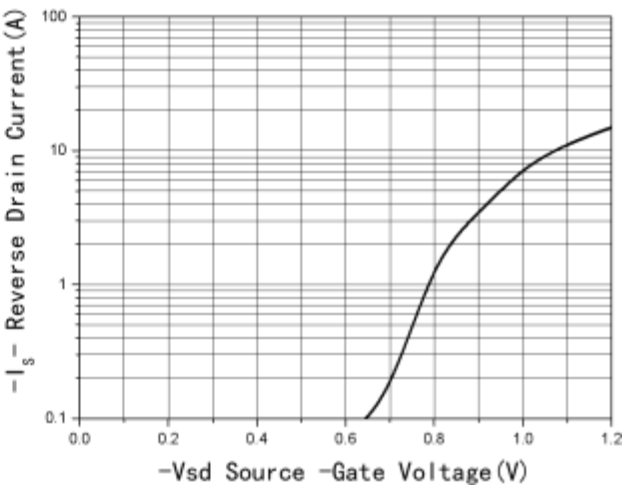


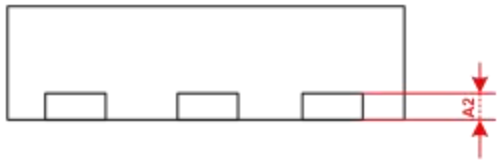
Fig6 Gate Charge


Power Dissipation (W)
3.0
2.7
2.4
2.1
1.8
1.5
1.2
0.9
0.6
0.3
0.0
0
15
30
45
60
75
90
105
120
135
150
TJ-Junction Temperature(°C)


-Is- Reverse Drain Current(A)
100
10
1
0.1
0.0
0.2
0.4
0.6
0.8
1.0
1.2
-Vsd Source -Gate Voltage(V)

Package Information

DFN2*2-6L-B



SIDE VIEW

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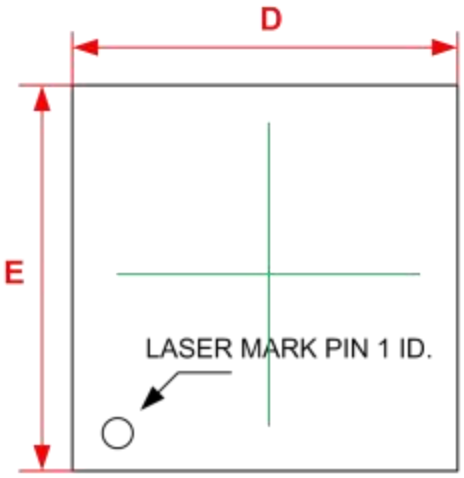
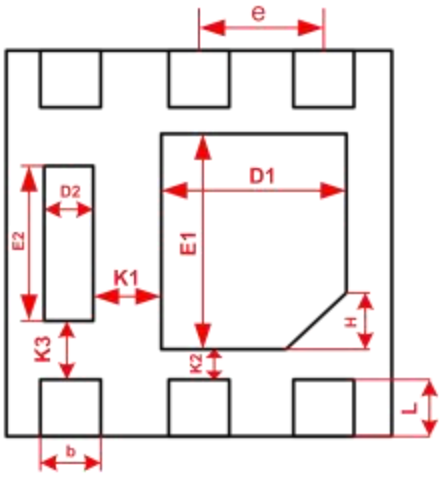


TOP VIEW



BOTTOM VIEW

Common Dimension (mm)			
PKG	DFN2020-6L-B		
SYMBOL	MIN.	MON.	MAX.
A	0.527	0.552	0.577
A2		0.127REF	
b	0.25	0.30	0.35
D	1.90	2.00	2.10
E	1.90	2.00	2.10
D1	0.85	0.95	1.05
E1	1.05	1.15	1.25
D2	0.20	0.25	0.30
E2	0.69	0.79	0.89
e	0.55	0.65	0.75
H	0.25	0.30	0.35
K1	0.25MIN		
K2	0.15MIN		
K3	0.20MIN		
L	0.20	0.25	0.30

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